

Ordering number : ENN7151

N-Channel Silicon MOSFET



**2SK3413LS**

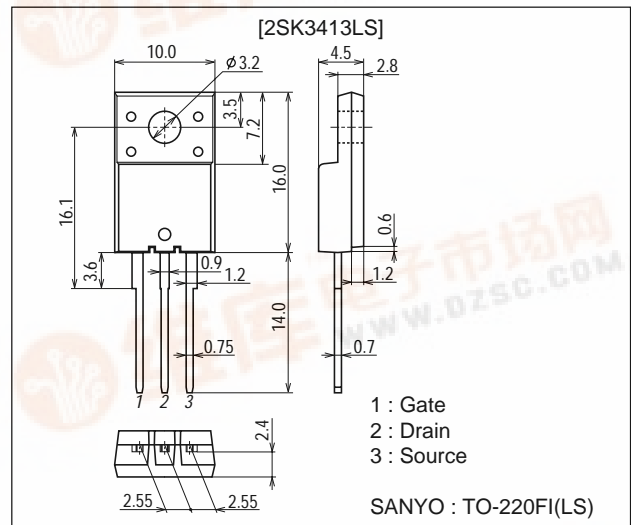
**DC / DC Converter Applications**

**Features**

- Low ON-resistance.
- 4V drive.

**Package Dimensions**

unit : mm  
2078C



**Specifications**

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		25	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	100	A
Allowable Power Dissipation	P <sub>D</sub>		2.0	W
		Tc=25°C	25	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.0		2.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =12A	16			S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =12A, V <sub>GS</sub> =10V		25	33	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =12A, V <sub>GS</sub> =4V		35	49	mΩ

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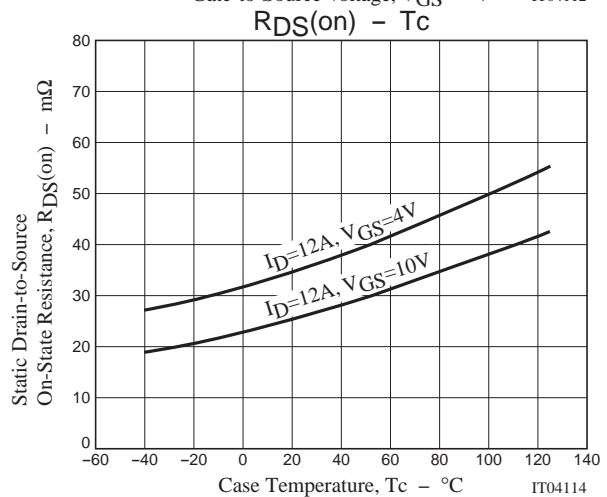
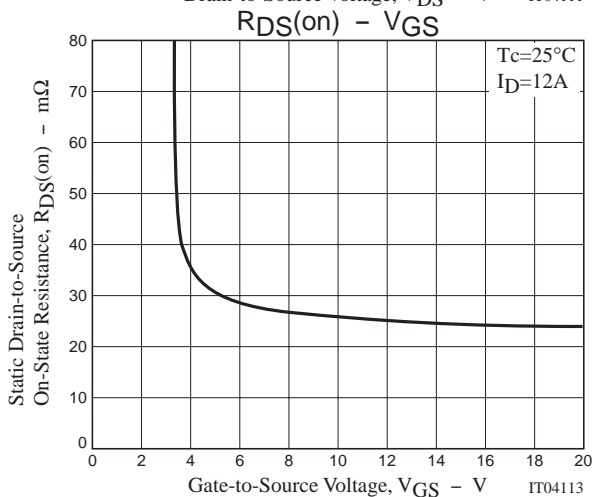
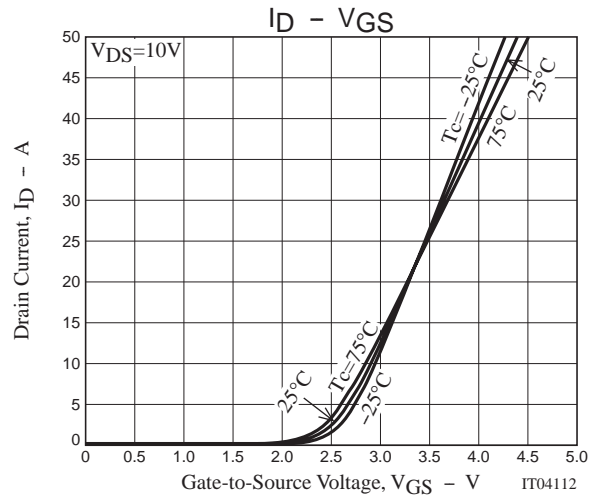
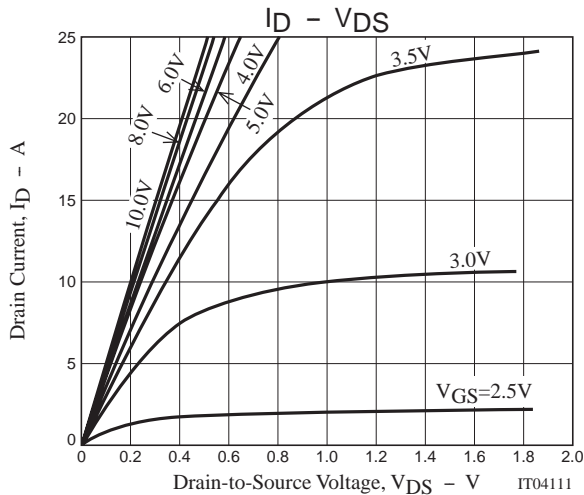
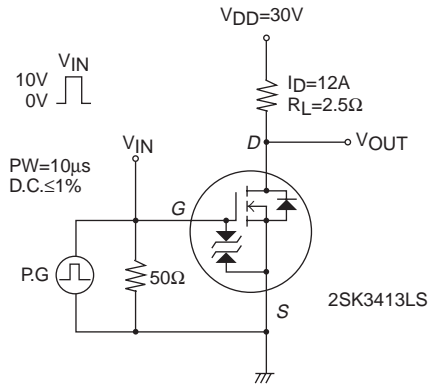


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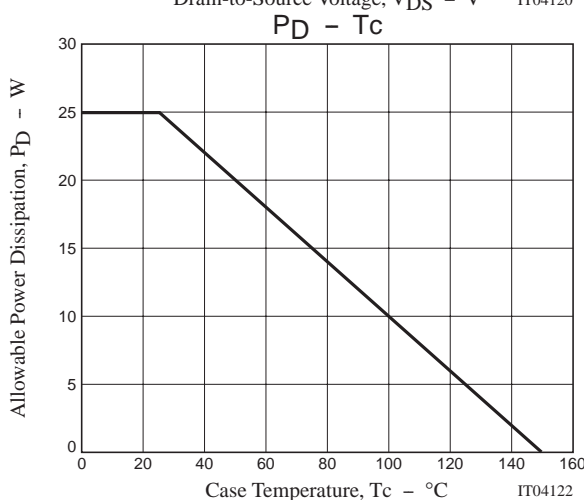
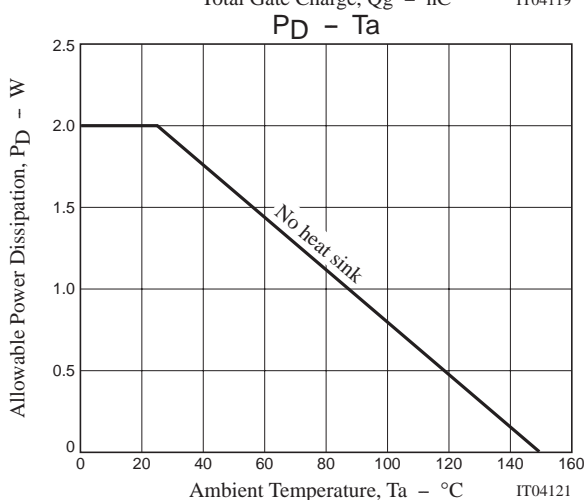
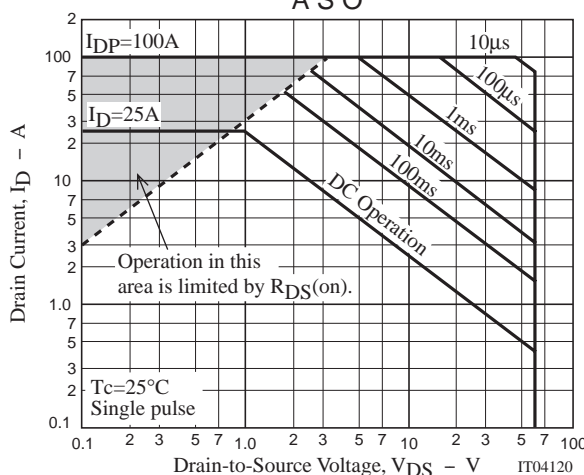
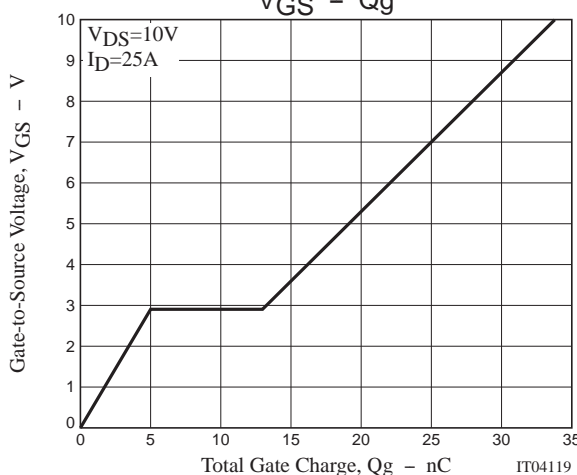
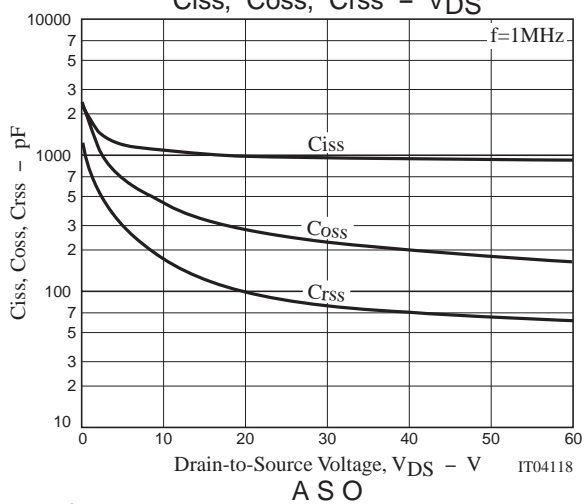
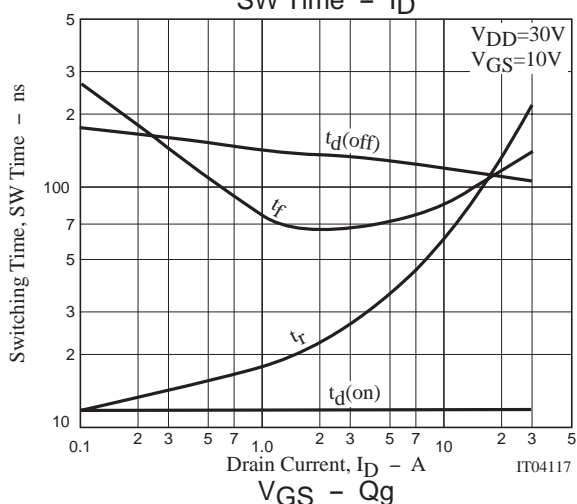
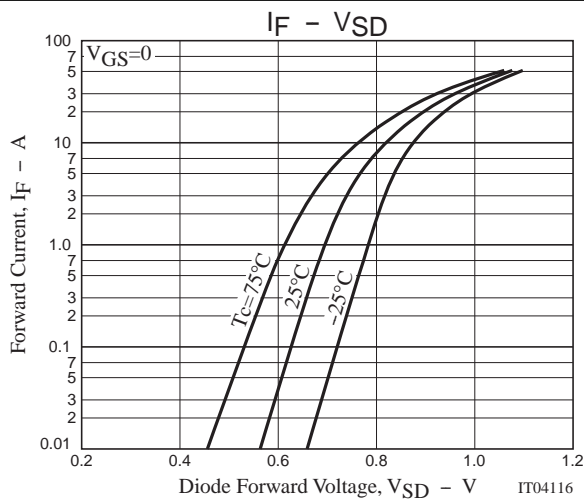
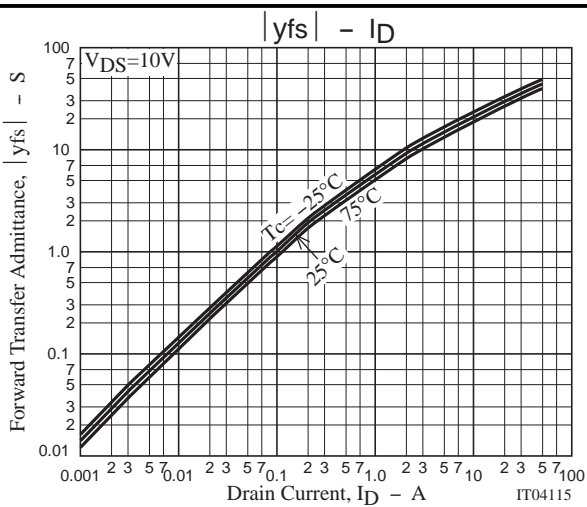
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		1000		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		280		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		100		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		12		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		72		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		120		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		90		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =25A		34		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =25A		5		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =25A		8		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =25A, V <sub>GS</sub> =0	0.93		1.2	V

## Switching Time Test Circuit



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